

Appl. No. 09/902,277

CLAIMS

46
35. (Amended) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine-containing layer proximate the polycrystalline thin film transistor layer, the fluorine-containing layer comprising tungsten; and

transferring fluorine into the polycrystalline thin film transistor layer from the fluorine-containing layer.

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34. The method of claim 33 wherein the polycrystalline thin film transistor layer comprises silicon.

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35. (Amended) The method of claim 33 wherein the forming a fluorine-containing layer comprises chemical vapor deposition utilizing WF₆ and SiH₄ precursors.

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36. (Amended) The method of claim 35 further comprising, after the transferring fluorine, removing the fluorine-containing layer from over the thin film transistor layer.

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S9 37. (Amended) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine-containing layer over the transistor gate and over the polycrystalline thin film transistor layer;

providing a buffering layer intermediate the thin film transistor layer and the fluorine-containing layer; and

transferring fluorine into the polycrystalline thin film transistor layer over the transistor gate from the fluorine-containing layer.

S1
E1
ENC 38. (New) The method of claim 37 wherein the fluorine-containing layer comprises tungsten.

S2
E2 39. (New) The method of claim 37 wherein the buffering layer comprises SiO_2 .

S3
E3 40. (New) The method of claim 37 wherein the polycrystalline thin film transistor layer comprises germanium.
